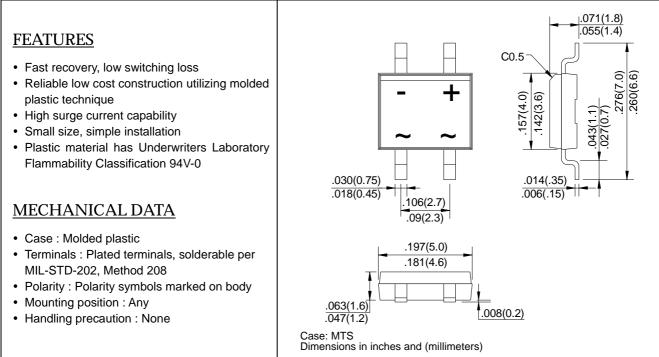


## VI. Bridge Rectifier

## SMD Glass Passivated Bridge Rectifier (Fast Recovery, Low Profile Type) RMD1S~RMD7S (Package: MTS)



## **Ratings & Electrical Characteristics**

Ratings at 25 ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristics	Symbol	RMD 1S	RMD 2S	RMD 3S	RMD 4S	RMD 5S	RMD 6S	RMD 7S	Units
Maximum recurrent peak reverse voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current on glass-epoxy P.C.B. (Note 2) on aluminum substrate (Note 3)	lo				0.5 0.8				Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load, (JEDEC Method)	I <sub>FSM</sub>				25				Amps
Maximum forward voltage at 0.4A DC and at 25	V <sub>F</sub>	1.3							Volts
Maximum reverse current Ta=25 at rated DC blocking voltage Ta=125	I <sub>R</sub>	5.0 500							μΑ
Typical junction capacitance (Note 1)	Cj	13							PF
Maximum reverse recovery time (Note 4)	Trr		15	50		250	50	00	ns
Typical thermal resistance (Note 3)	Rth-JA	70						/ W	
Typical thermal resistance (Note 2)	Rth-JL	20							/ W
Operating and storage temperature range	Tj, Tstg	-55 to +150							

Notes:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts D.C.

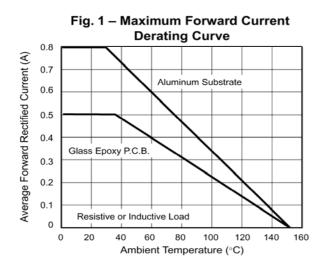
2. On glass epoxy P.C.B. mounted on 0.05 x 0.05" (1.3 x 1.3mm) pads.

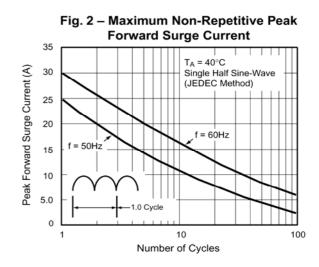
3. On aluminum substrate P.C.B. with an area of 0.8" x 0.8" (20 x 20mm) mounted on 0.05 x 0.05" (1.3 x 1.3mm) solder pad.

4. Reverse Recovery Test Conditions:  $I_F=0.5A$ ,  $I_R=1.0A$ ,  $I_{RR}=0.25A$ 



## **Ratings and Characteristic Curves of RMD1S~RMD7S**





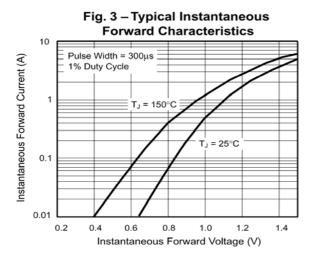


Fig. 4 - Typical Reverse Leakage Characteristics Per Leg

